

(19) **United States**
 (12) **Patent Application Publication** (10) **Pub. No.: US 2024/0213168 A1**
 WANG et al. (43) **Pub. Date: Jun. 27, 2024**

(54) **SEMICONDUCTOR PACKAGE AND METHOD OF MANUFACTURING THE SAME**

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(21) Appl. No.: **18/434,711**

(22) Filed: **Feb. 6, 2024**

Related U.S. Application Data

- (63) Continuation of application No. 17/109,111, filed on Dec. 1, 2020, now Pat. No. 11,894,308, which is a continuation of application No. 16/109,272, filed on Aug. 22, 2018, now Pat. No. 10,854,550.
 (60) Provisional application No. 62/564,939, filed on Sep. 28, 2017.

Publication Classification

- (51) **Int. Cl.**
H01L 23/538 (2006.01)
H01L 21/48 (2006.01)
H01L 21/683 (2006.01)
H01L 23/00 (2006.01)
H01L 23/31 (2006.01)
H01L 23/367 (2006.01)
H01L 23/66 (2006.01)
H01L 25/065 (2006.01)
H01P 3/06 (2006.01)

- (52) **U.S. Cl.**
 CPC **H01L 23/5386** (2013.01); **H01L 21/4857** (2013.01); **H01L 21/6835** (2013.01); **H01L 23/3107** (2013.01); **H01L 23/3677** (2013.01); **H01L 23/5383** (2013.01); **H01L 23/66** (2013.01); **H01P 3/06** (2013.01); **H01L 23/3128** (2013.01); **H01L 24/16** (2013.01); **H01L 24/48** (2013.01); **H01L 25/0657** (2013.01); **H01L 2221/68345** (2013.01); **H01L 2221/68359** (2013.01); **H01L 2223/6622** (2013.01); **H01L 2224/16225** (2013.01); **H01L 2224/32145** (2013.01); **H01L 2224/48225** (2013.01); **H01L 2224/73253** (2013.01); **H01L 2225/0651** (2013.01); **H01L 2225/06517** (2013.01); **H01L 2225/06558** (2013.01); **H01L 2924/15313** (2013.01); **H01L 2924/19041** (2013.01); **H01L 2924/19042** (2013.01); **H01L 2924/19043** (2013.01); **H01L 2924/19103** (2013.01); **H01L 2924/19105** (2013.01)

(57) **ABSTRACT**

The present disclosure provides a semiconductor substrate, including a first dielectric layer with a first surface and a second surface, a first conductive via extending between the first surface and the second surface, a first patterned conductive layer on the first surface, and a second patterned conductive layer on the second surface. The first conductive via includes a bottom pattern on the first surface and a second patterned conductive layer on the second surface. The bottom pattern has at least two geometric centers corresponding to at least two geometric patterns, respectively, and a distance between one geometric center and an intersection of the two geometrical patterns is a geometric radius. A distance between the at least two geometric centers is greater than 1.4 times the geometric radius. A method for manufacturing the semiconductor substrate described herein and a semiconductor package structure having the semiconductor substrate are also provided.

